



600mA LOW DROPOUT LINEAR REGULATOR

Features

- Low Dropout Voltage of 600mV at 600mA
- Guaranteed 600mA Output Current
- Very Low Quiescent Current at about 30uA
- Max. $\pm 2\%$ Output Accuracy
- Needs Only $1\mu\text{F}$ Capacitor for Stability
- Thermal Shutdown Protection
- Current Limit Protection
- Low-ESR Ceramic Capacitor for Output Stability
- RoHS Compliant

Applications

- DVD/CD-ROMs, CD/RWs
- Wireless Devices
- LCD Modules
- Battery Power Systems
- Card Readers
- XDSL Routers

Description

The APE8805 series are low dropout, positive linear regulators with very low quiescent current. The APE8805 can supply 600mA output current with a low dropout voltage at about 600mV.

The APE8805 regulator is able to operate with output capacitors as small as $1\mu\text{F}$ for stability. Other than the current limit protection APE8805 also offers on chip thermal shutdown feature providing protection against overload or any condition when the ambient temperature exceeds the junction temperature.

The APE8805 series are available in fixed output voltage ranging from 1.8 volt, 2.5 volt and 3.3 volt. The APE8805 series are available in space-saving SOT-23, SOT-89, and SOT-223 packages.

Typical Application Circuit

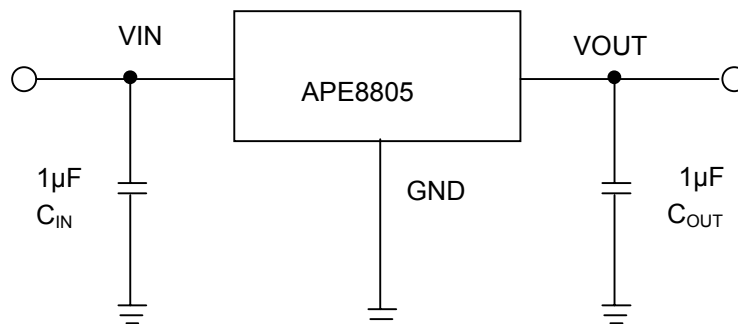
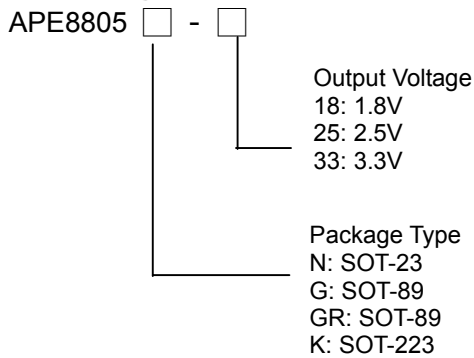


Figure 1. Typical Application Circuit of APE8805

Note : To prevent oscillation, it is recommended to use minimum $1\mu\text{F}$ X7R or X5R dielectric capacitors if ceramics are used as input/output capacitors.



Ordering Information



Note : The devices are available in fixed voltages range of 1.8V , 2.5V& 3.3V. Please consult APEC sales office or authorized distributor for availability of special output voltages.

Pin Assignments

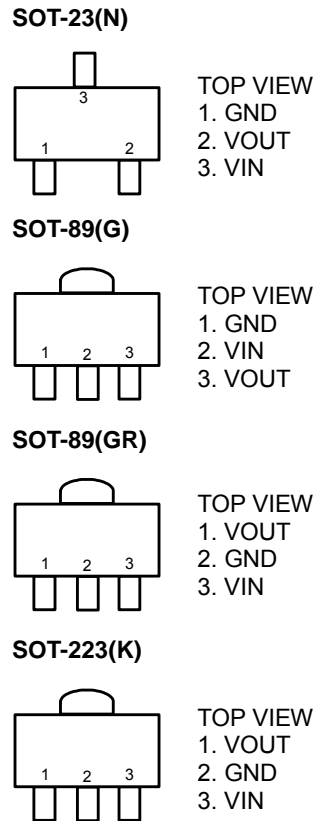


Figure 2. Pin Assignment of APE8805

Absolute Maximum Ratings

Parameter	Symbol	Min	Max	Unit
Supply Input Voltage	V _{IN}		6	V
Maximum Junction Temperature	T _J		150	°C
Power Dissipation SOT-23	P _D		0.4	W
Power Dissipation SOT-89	P _D		0.57	W
Power Dissipation SOT-223	P _D		0.74	W
Package Thermal Resistance SOT-23	θ _{JA}		250	°C/W
Package Thermal Resistance SOT-89	θ _{JA}		175	°C/W
Package Thermal Resistance SOT-223	θ _{JA}		135	°C/W
Storage Temperature Range	T _S	-65	150	°C
Lead Temperature (Soldering, 10 sec.)	T _{LEAD}		260	°C

Note : Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device.



Recommended Operating Conditions

Parameter	Symbol	Min	Max	Unit
Input Voltage	V_{IN}	2.8	5.5	V
Operating Junction Temperature Range	T_J	-40	125	°C
Ambient Temperature Range	T_A	-40	125	°C

Electrical Characteristics

($V_{IN}=V_{OUT}+1V$ or $V_{IN}=2.8V$ whichever is greater, $C_{IN}=1\mu F$, $C_{OUT}=1\mu F$, $T_A=25\text{ °C}$, unless otherwise specified)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Output Voltage Accuracy	ΔV_{OUT}	$I_O = 1mA$	-2		+2	%
Current Limit	I_{LIMIT}	$R_{Load}=1\Omega$	600			mA
Quiescent Current	I_Q	$I_O = 0mA$		30	50	μA
Dropout Voltage (Note 1)	V_{DROP}	$1.2V \leq V_{OUT} \leq 2.0V$		1400		mV
		$I_O=600mA$ $2.0V < V_{OUT} \leq 2.8V$		800		
		$2.8V < V_{OUT} \leq 4.5V$		600		
Line Regulation	ΔV_{LINE}	$I_O=1mA$, $V_{IN}=V_{OUT} + 1V$ to 5V		1	5	mV
Load Regulation (Note 2)	ΔV_{LOAD}	$I_O=0mA$ to 600mA		13	50	mV
Ripple Rejection	PSRR	$V_{IN}=V_{OUT}+1V$ $f_{RIPPLE} = 120Hz$, $C_{OUT} = 1\mu F$		60		dB
Temperature Coefficient	TC	$I_{OUT} = 1mA$, $V_{IN} = 5V$		50		ppm/ °C
Thermal Shutdown Temperature	TSD			160		°C
Thermal Shutdown Hysteresis	ΔTSD			25		°C

Note 1 : The dropout voltage is defined as $V_{IN}-V_{OUT}$, which is measured when V_{OUT} drop about 100mV.

Note 2 : Regulation is measured at a constant junction temperature by using 40ms current pulse and load regulation in the load range from 0mA to 600mA.

Functional Pin Description

Pin Name	Pin Function
VIN	Power is supplied to this device from this pin which is required an input filter capacitor. In general, the input capacitor in the range of 1 μF to 10 μF is sufficient.
VOUT	The output supplies power to loads. The output capacitor is required to prevent output voltage unstable. The APE8805 is stable with an output capacitor 1 μF or greater. The larger output capacitor will be required for application with large transit load to limit peak voltage transits, besides could reduce output noise, improve stability, PSRR.
GND	Common ground pin



Block Diagram

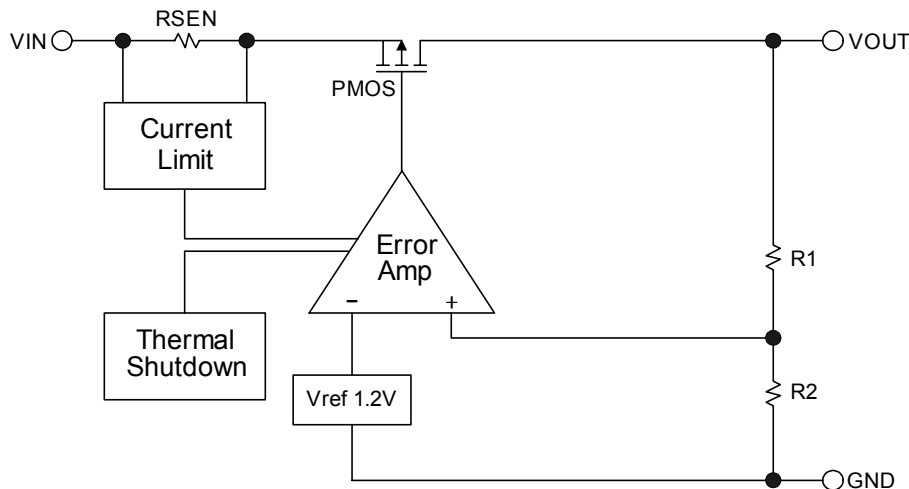


Figure 3. Block Diagram of APE8805

Application Information

The APE8805 series are low dropout linear regulators that could provide 600mA output current at dropout voltage about 600mV. Besides, current limit and on chip thermal shutdown features provide protection against any combination of overload or ambient temperature that could exceed junction temperature.

1. Output and Input Capacitor

The APE8805 regulator is designed to be stable with a wide range of output capacitors. The ESR of the output capacitor affects stability. Larger value of the output capacitor decreases the peak deviations and provides to improve transition response for larger current changes. The capacitor types (aluminum, ceramic, and tant- alum) have different characterizations such as temperature and voltage coefficients. All ceramic capacitors are manufactured with a variety of dielectrics, each with different behavior across temperature and applications. Common dielectrics used are X5R, X7R and Y5V. It is recommended to use 1uF to 10uF X5R or X7R dielectric ceramic capacitors with 30mΩ to 50mΩ ESR range between device outputs to ground for transient stability. The APE8805 is designed to be stable with low ESR ceramic capacitors and higher values of capacitors and ESR could improve output stability. So the

ESR of output capacitor is very important because it generates a zero to provide phase lead for loop stability.

There are no requirements for the ESR on the input capacitor, but its voltage and temperature coefficient have to be considered for device application environment.

2. Protection Features

In order to prevent overloading or thermal condition from damaging device, APE8805 regulator has internal thermal and current limiting functions designed to protect the device. It will rapidly shut off PMOS pass element during overloading or over temperature condition.

3. Thermal Consideration

The power handling capability of the device will be limited by maximum operation junction temperature (125°C). The power dissipated by the device will be estimated by $PD = I_{OUT} \times (V_{IN} - V_{OUT})$. The power dissipation should be lower than the maximum power dissipation listed in "Absolute Maximum Ratings" section.



Typical Performance Curves

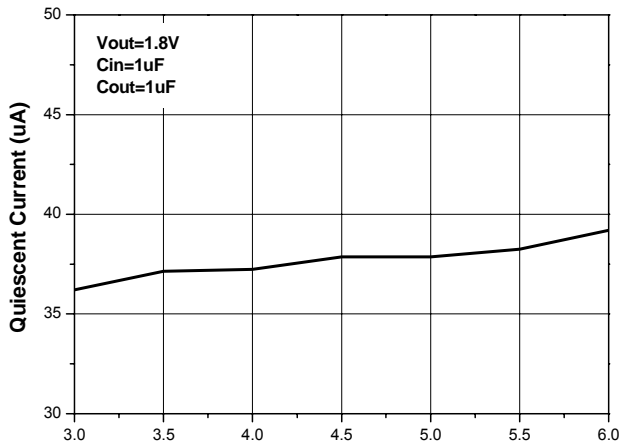


Figure 4. Quiescent Current vs. Input Voltage

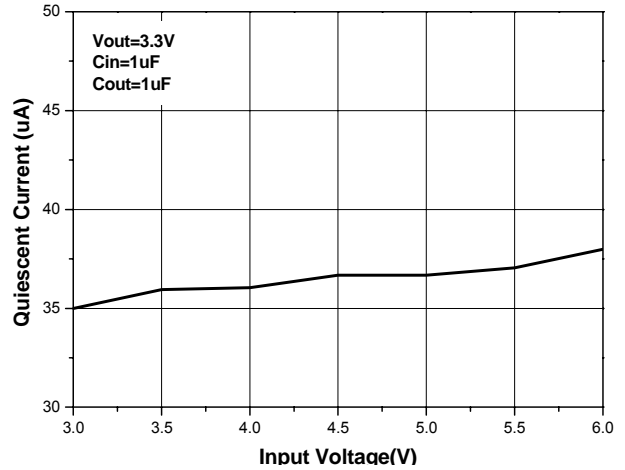


Figure 5. Quiescent Current vs. Input Voltage

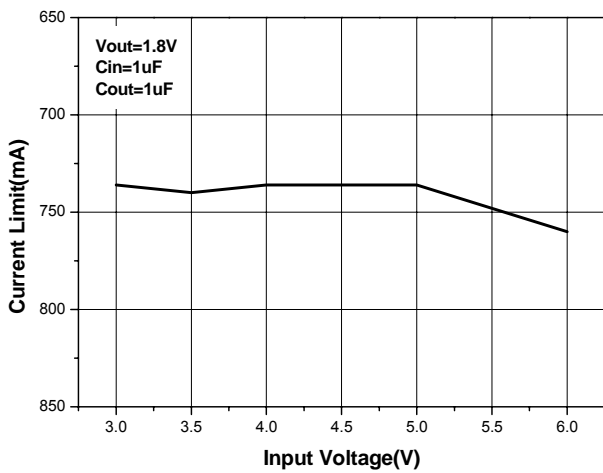


Figure 6. Current limit vs. Input Voltage

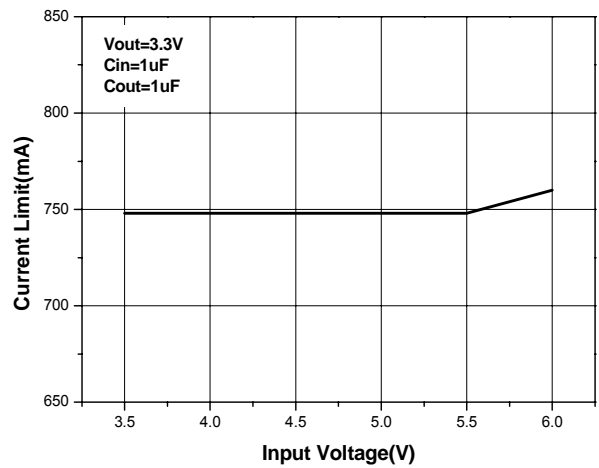


Figure 7. Current Limit vs. Input Voltage

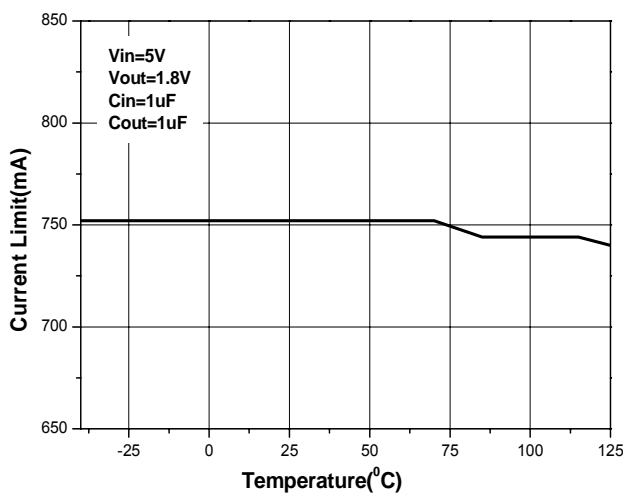


Figure 8. Current limit vs. Temperature

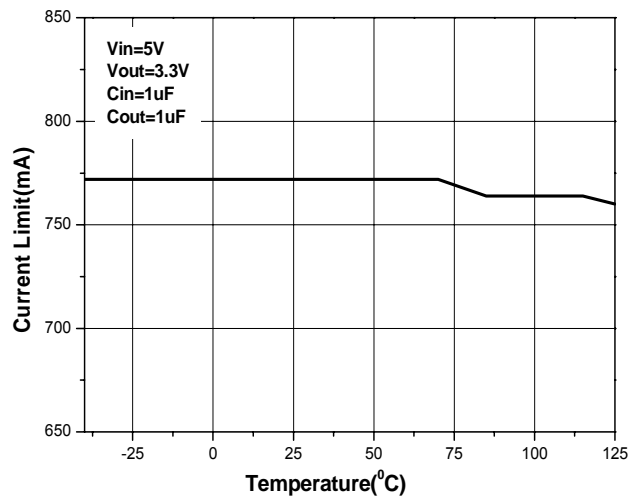


Figure 9. Current limit vs. Temperature



Typical Performance Curves (Continued)

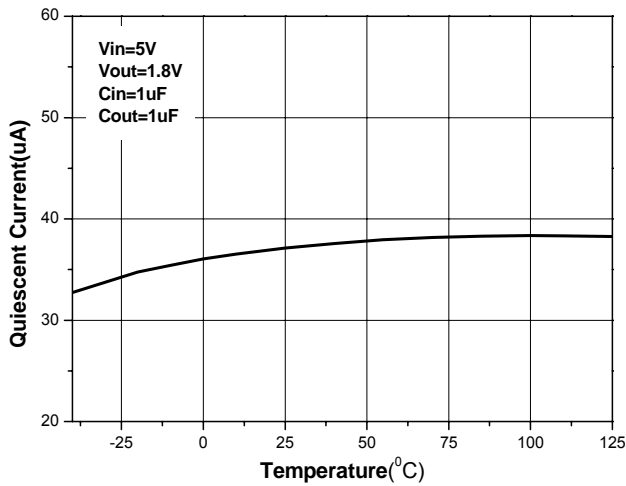


Figure 10. Quiescent Current vs. Temperature

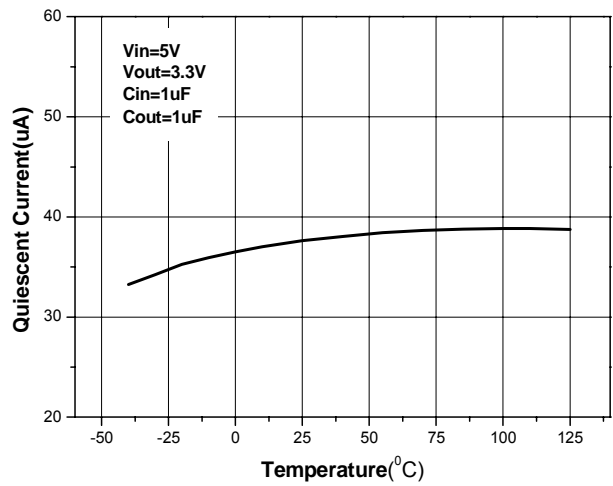


Figure 11. Quiescent Current vs. Temperature

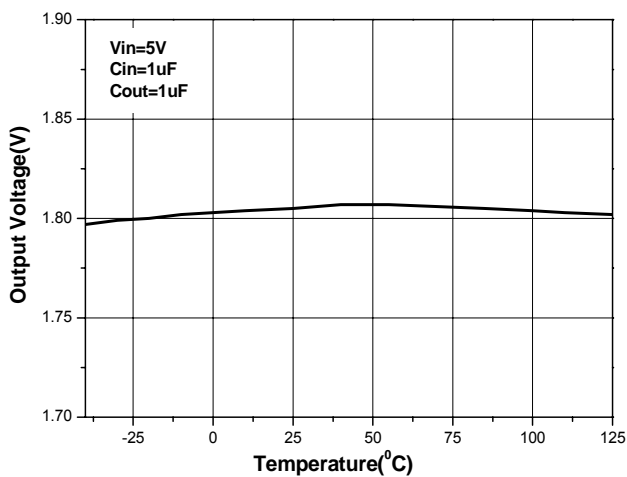


Figure 12. Temperature Stability

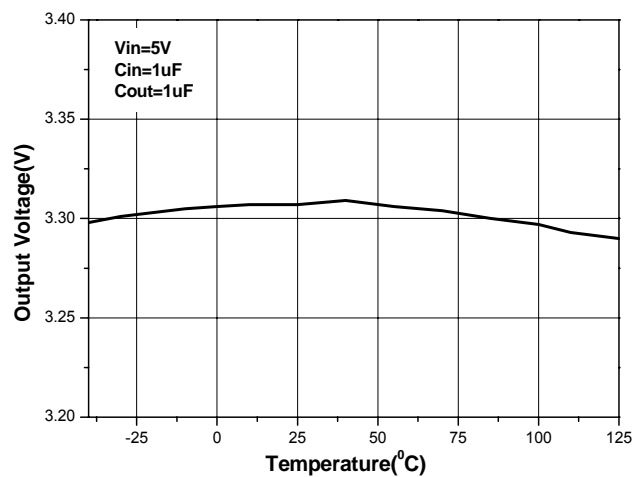


Figure 13. Temperature Stability

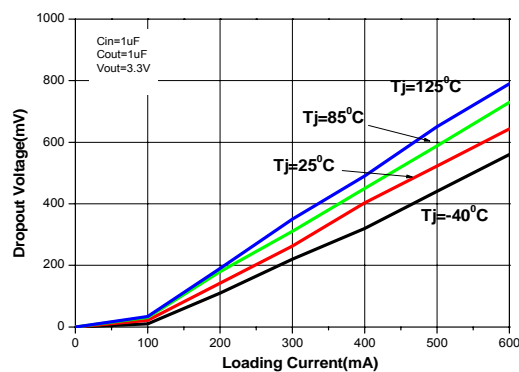


Figure 14. Dropout Voltage vs. Loading Current



Typical Performance Curves (Continued)

$V_{IN}=4V$ $I_{OUT}=1mA$ to $150mA$
 $V_{OUT}=3.3V$ $C_{IN}=1\mu F$ $C_{OUT}=1\mu F$

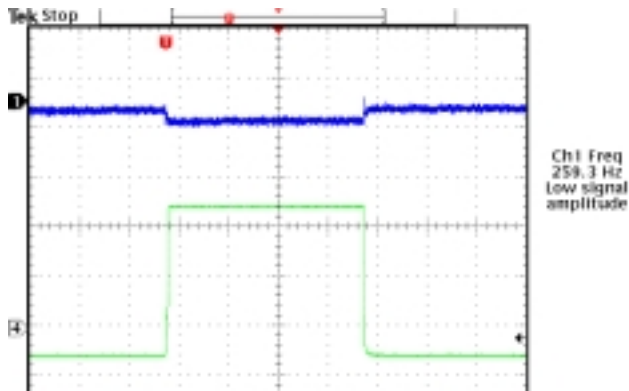


Figure 15. Load Transition Response

$V_{IN}=4V$ $I_{OUT}=1mA$ to $150mA$
 $V_{OUT}=3.3V$ $C_{IN}=1\mu F$ $C_{OUT}=4.7\mu F$

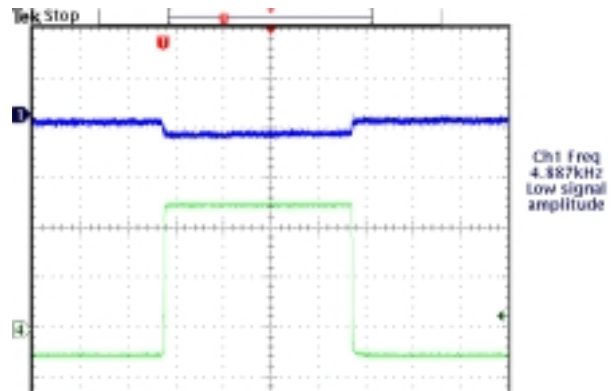


Figure 16. Load Transition Response

$V_{IN}=3V$ to $4V$ $I_{OUT}=10mA$ $V_{OUT}=1.8V$ $C_{IN}=1\mu F$ $C_{OUT}=1\mu F$

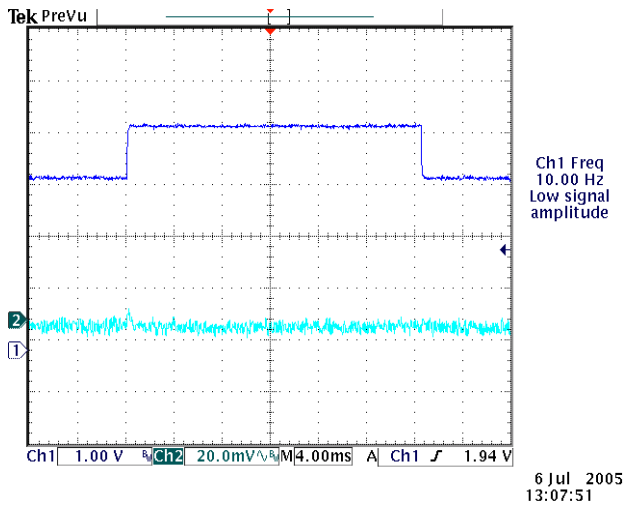


Figure 17. Line Transition Response

$V_{IN}=3V$ to $4V$ $I_{OUT}=10mA$ $V_{OUT}=1.8V$ $C_{IN}=1\mu F$ $C_{OUT}=4.7\mu F$

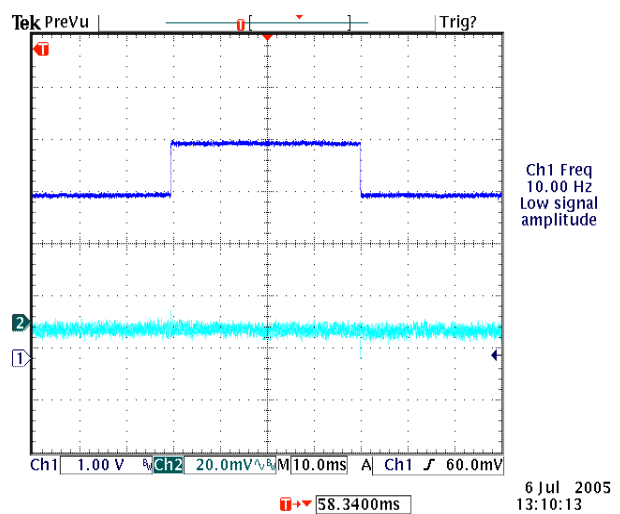
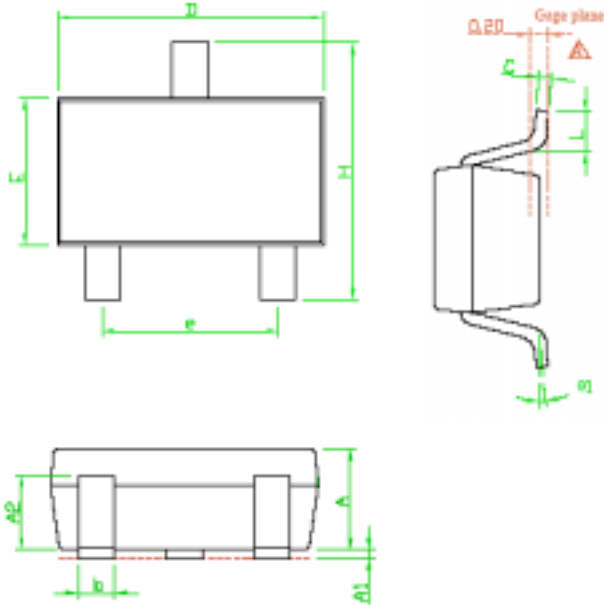


Figure 18. Line Transition Response



Outline Information

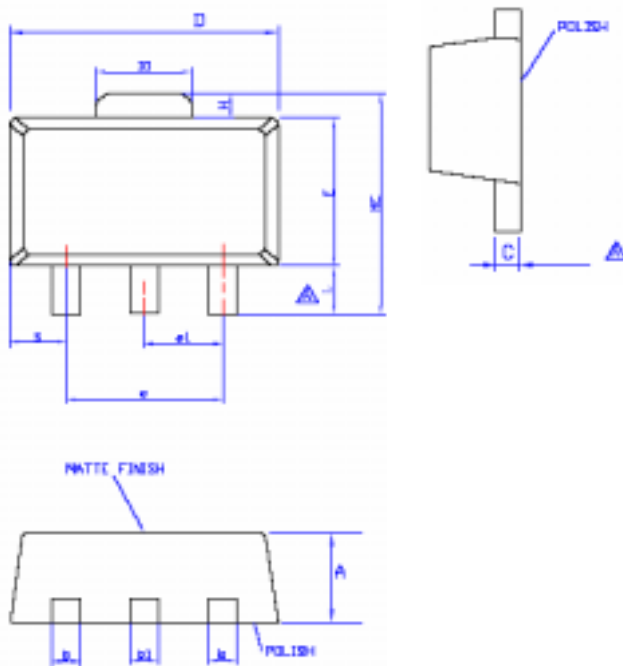
SOT-23 Package (Unit: mm)



SYMBOLS UNIT	DIMENSION IN MILLIMETER		
	MIN	NOM	MAX
A	1.00	1.10	1.30
A1	0.00	---	0.10
A2	0.70	0.80	0.90
b	0.35	0.40	0.50
C	0.10	0.15	0.25
D	2.70	2.90	3.10
E	1.40	1.60	1.80
e	---	1.90(TYP)	---
H	2.60	2.80	3.00
L	0.37	---	---
θ1	1°	5°	9°

- Note 1 : Package Body Sizes Exclude Mold Flash Protrusions or Gate Burrs.
- Note 2 : Tolerance ± 0.1000 mm(4mil) Unless Otherwise Specified.
- Note 3 : Coplanarity : 0.1000 mm
- Note 4 : Dimension L Is Measured in Gage plane.

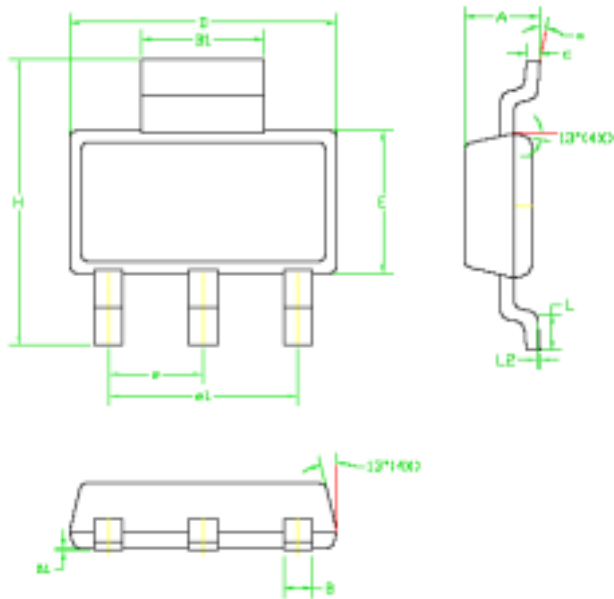
SOT-89 Package (Unit: mm)



SYMBOLS UNIT	DIMENSION IN MILLIMETER		
	MIN	NOM	MAX
A	1.40	1.50	1.60
L	0.89	1.04	1.20
b	0.36	0.42	0.48
b1	0.41	0.47	0.53
C	0.38	0.40	0.43
D	4.40	4.50	4.60
D1	1.40	1.60	1.75
HE	---	---	4.25
E	2.40	2.50	2.60
e	2.90	3.00	3.10
H	0.35	0.40	0.45
S	0.65	0.75	0.85
e1	1.40	1.50	1.60



SOT-223 Package (Unit: mm)

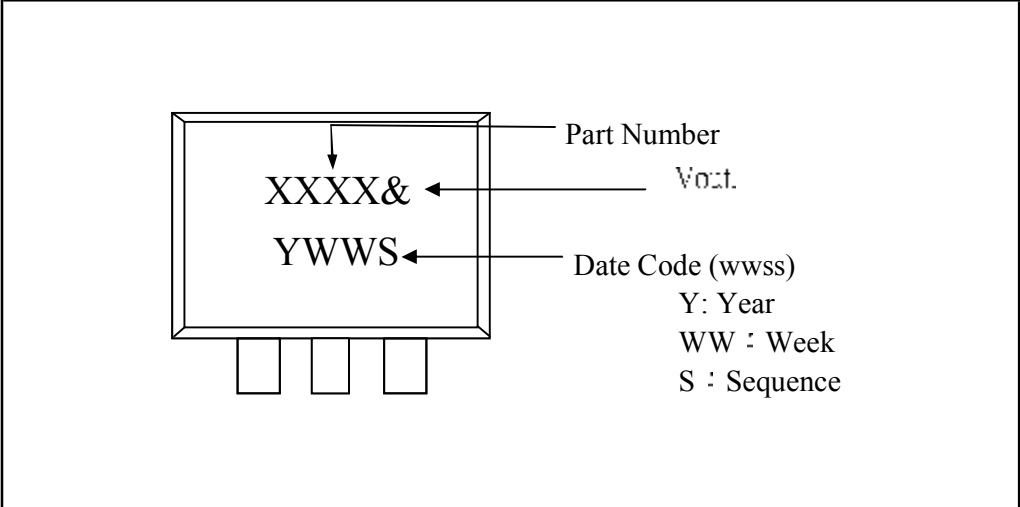


SYMBOLS UNIT	DIMENSION IN MILLIMETER		
	MIN	NOM	MAX
A	1.55		1.80
A1	0.02		0.12
B	0.60		0.80
B1	2.90		3.10
c	0.24		0.32
D	6.30		6.70
E	3.30		3.70
e	2.30 BSC		
e1	4.60 BSC		
H	6.70		7.30
L	0.90 MIN		
L2	0.06 BSC		
α	0°		10°

Life Support Policy

APEC's products are not authorized for use as critical components in life support devices or other medical systems.

Part Marking Information : SOT-89



Test Report

MEICER SEMICONDUCTOR INC.

NO. 1, DING AN RD., JUNG LI INDUSTRIAL PARK, JUNG LI
CITY, TAIWAN, R. O. C.

Report No. : CE/2005/C5149

Date : 2005/12/26

Page : 1 of 7

The following merchandise was (were) submitted and identified by the client as :

Type of Product : IC
Style/Item No : SOT SERIES (SOT2X, SOT89, SOT223, SC82)
Sample Received : 2005/12/19
Testing Date : 2005/12/19 TO 2005/12/26

=====

Test Result : - Please see the next page -


Daniel Yeh, M.R. / Operation Manager
Signed for and on behalf of
SGS TAIWAN LTD.

Test Report

MEICER SEMICONDUCTOR INC.

NO. 1, DING AN RD., JUNG LI INDUSTRIAL PARK, JUNG LI CITY, TAIWAN, R. O. C.

Report No. : CE/2005/C5149

Date : 2005/12/26

Page : 2 of 7

Test Result

PART NAME NO.1 : MIXED ALL PARTS

Test Item (s):	Unit	Method	MDL	Result
				No.1
Asbestos				
Anthrophyllite(CAS NO.017068-78-9)	%	As per NIOSH 9000 method. Analysis was performed by XRD.	1	Negative
Crocidolite(CAS NO.012001-28-4)	%	As per NIOSH 9000 method. Analysis was performed by XRD.	1	Negative
Amosite(CAS NO.012172-73-5)	%	As per NIOSH 9000 method. Analysis was performed by XRD.	1	Negative
Tremolite(CAS NO.014567-73-8)	%	As per NIOSH 9000 method. Analysis was performed by XRD.	1	Negative
Chrysotile(CAS NO.012001-29-5)	%	As per NIOSH 9000 method. Analysis was performed by XRD.	1	Negative
Actinolite(CAS NO.013768-00-8)	%	As per NIOSH 9000 method. Analysis was performed by XRD.	1	Negative

Test Item (s):	Unit	Method	MDL	Result
				No.1
AZO		As per LMBG 8202-2		
4-AMINODIPHENYL (CAS NO.92-67-1)	ppm	Analysis was performed by GC/MS.	3	N.D.
BENZIDINE (CAS NO.92-87-5)	ppm	Analysis was performed by GC/MS.	3	N.D.
4-CHLORO-O-TOLUIDINE (CAS NO.95-69-2)	ppm	Analysis was performed by GC/MS.	3	N.D.
2-NAPHTHYLAMINE (CAS NO.91-59-8)	ppm	Analysis was performed by GC/MS.	3	N.D.
O-AMINOAZOTOLUENE (CAS NO.97-56-3)	ppm	Analysis was performed by GC/MS.	3	N.D.

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Date : 2005/12/26

Page : 3 of 7

Test Item (s):	Unit	Method	MDL	Result
				No.1
2-AMINO-4-NITROTOLUENE (CAS NO.99-55-8)	ppm	Analysis was performed by GC/MS.	3	N.D.
P-CHLOROANILINE (CAS NO.106-47-8)	ppm	Analysis was performed by GC/MS.	3	N.D.
2,4-DIAMINOANISOLE (CAS NO.615-05-4)	ppm	Analysis was performed by GC/MS.	3	N.D.
4,4'- DIAMINODIPHENYLMETHAN E (CAS NO.101-77-9)	ppm	Analysis was performed by GC/MS.	3	N.D.
3,3'-DICHLOROBENZIDINE (CAS NO.91-94-1)	ppm	Analysis was performed by GC/MS.	3	N.D.
3,3'-DIMETHOXYBENZIDINE (CAS NO.119-90-4)	ppm	Analysis was performed by GC/MS.	3	N.D.
3,3'-DIMETHYLBENZIDINE (CAS NO.119-93-7)	ppm	Analysis was performed by GC/MS.	3	N.D.
3,3'-DIMETHYL-4,4'- DIAMINODIPHENYLMETHAN E (CAS NO.838-88-0)	ppm	Analysis was performed by GC/MS.	3	N.D.
P-CRESIDINE(2-METHOXY- 5-METHYLANILINE) (CAS NO.120-71-8)	ppm	Analysis was performed by GC/MS.	3	N.D.
4,4'-METHYLENE-BIS-(2- CHLOROANILINE) (CAS NO.101-14-4)	ppm	Analysis was performed by GC/MS.	3	N.D.
4,4'-OXYDIANILINE (CAS NO.101-80-4)	ppm	Analysis was performed by GC/MS.	3	N.D.
4,4'-THIODIANILINE (CAS NO.139-65-1)	ppm	Analysis was performed by GC/MS.	3	N.D.
O-TOLUIDINE (CAS NO.95- 53-4)	ppm	Analysis was performed by GC/MS.	3	N.D.
2,4-TOLUYLENEDIAMINE (CAS NO.95-80-7)	ppm	Analysis was performed by GC/MS.	3	N.D.
2,4,5-TRIMETHYLANILINE (CAS NO.137-17-7)	ppm	Analysis was performed by GC/MS.	3	N.D.

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Page : 4 of 7

Test Item (s):	Unit	Method	MDL	Result
				No.1
O-ANISIDINE (CAS NO.90-04-0)	ppm	Analysis was performed by GC/MS.	3	N.D.
P-AMINOAZOBENZENE (CAS NO.60-09-3)	ppm	Analysis was performed by GC/MS.	3	N.D.

Test Item (s):	Unit	Method	MDL	Result
				No.1
Chlorinated Paraffin (C10~C13) (CAS NO:010871-26-2)	%	With reference to USEPA3540C or USEPA3550C. Analysis was performed by GC/MS or GC/ECD.	0.01	N.D.

Test Item (s):	Unit	Method	MDL	Result
				No.1
Formaldehyde(CAS No:000050-00-0)	ppm	With reference to DIN 53315 & USEPA 8315A. Analysis was performed by	0.2	N.D.

Test Item (s):	Unit	Method	MDL	Result
				No.1
Mirex(CAS NO:002385-85-5)	ppm	Analysis was performed by GC/MS.	4	N.D.

Test Item (s):	Unit	Method	MDL	Result
				No.1
Organic-tin compounds				
Triphenyl Tin(TPT)(CAS NO:000668-34-8)	ppm	With reference to 89/677/EEC & DIN 38407. Analysis was performed by GC/FPD.	0.03	N.D.
Tributyl Tin(TBT)	ppm	With reference to 89/677/EEC & DIN 38407. Analysis was performed by GC/FPD.	0.03	N.D.

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Page : 5 of 7

Test Item (s):	Unit	Method	MDL	Result
				No.1
Polychlorinated Naphthalene	ppm	With reference to USEPA 8081B. Analysis was performed by GC/MS.	5	N.D.

Test Item (s):	Unit	Method	MDL	Result
				No.1
Monobromobiphenyl	%	With reference to USEPA3540C or USEPA3550C. Analysis was performed by HPLC/DAD, LC/MS or GC/MS. (prohibited by 2002/95/EC (RoHS), 83/264/EEC, and 76/769/EEC)	0.0005	N.D.
Dibromobiphenyl	%		0.0005	N.D.
Tribromobiphenyl	%		0.0005	N.D.
Tetrabromobiphenyl	%		0.0005	N.D.
Pentabromobiphenyl	%		0.0005	N.D.
Hexabromobiphenyl	%		0.0005	N.D.
Heptabromobiphenyl	%		0.0005	N.D.
Octabromobiphenyl	%		0.0005	N.D.
Nonabromobiphenyl	%		0.0005	N.D.
Decabromobiphenyl	%		0.0005	N.D.
Total PBBs (Polybrominated biphenyls)/Sum of above	%		-	N.D.
Monobromobiphenyl ether	%	With reference to USEPA3540C or USEPA3550C. Analysis was performed by HPLC/DAD, LC/MS or GC/MS. (prohibited by 2002/95/EC (RoHS), 83/264/EEC, and 76/769/EEC)	0.0005	N.D.
Dibromobiphenyl ether	%		0.0005	N.D.
Tribromobiphenyl ether	%		0.0005	N.D.
Tetrabromobiphenyl ether	%		0.0005	N.D.
Pentabromobiphenyl ether	%		0.0005	N.D.
Hexabromobiphenyl ether	%		0.0005	N.D.
Heptabromobiphenyl ether	%		0.0005	N.D.
Octabromobiphenyl ether	%		0.0005	N.D.
Nonabromobiphenyl ether	%		0.0005	N.D.
Decabromobiphenyl ether	%		0.0005	N.D.
Total PBBEs(PBDEs) (Polybrominated biphenyl ethers)/Sum of above	%		-	N.D.
Total of Mono to Nona-brominated biphenyl ether. (Note 4)	%		-	N.D.

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Date : 2005/12/26

Page : 6 of 7

Test Item (s):	Unit	Method	MDL	Result
				No.1
PCBs(Polychlorinated Biphenyls)(CAS NO:001336-36-3)	ppm	With reference to USEPA 8082A. Analysis was performed by GC/MS or GC/ECD.	0.5	N.D.

Test Item (s):	Unit	Method	MDL	Result
				No.1
PVC (CAS No:9002-86-2)	%	Analysis was performed by FTIR/ATR and Pyrolyzer-GC/MS.	1	Negative

Test Item (s):	Unit	Method	MDL	Result
				No.1
Chromium VI (Cr+6)	ppm	UV-VIS after reference to US EPA 3060A.	2	N.D.
Cadmium (Cd)	ppm	ICP-AES after reference to EN 1122, method B:2001 or other acid digestion.	2	N.D.
Mercury (Hg)	ppm	ICP-AES after reference to US EPA 3052 or other acid digestion.	2	N.D.
Lead (Pb)	ppm	ICP-AES after reference to US EPA 3050B or other acid digestion.	2	N.D.

- NOTE: (1) N.D. = Not detected (<MDL)
 (2) ppm = mg/kg
 (3) MDL = Method Detection Limit
 (4) Decabromodiphenyl ether (DecaBDE) in polymeric applications is exempted by Commission Decision of 13 Oct 2005 amending Directive 2002/95/EC notified under document 2005/717/EC.
 (5) PBBEs=PBDEs=Polybrominated Diphenyl Ethers=PBDOs=PBBOs.
 (6) " - " = Not Regulation
 (7) Negative = Undetectable / Positive = Detectable
 (8) Negative = < 1.0 %, Positive = > 1.0 %
 (9) The MDL is 5ppm for the single compound of CP

Test Report

MEICER SEMICONDUCTOR INC.

NO. 1, DING AN RD., JUNG LI INDUSTRIAL PARK, JUNG LI
CITY, TAIWAN, R. O. C.

Report No. : CE/2005/C5149

Date : 2005/12/26

Page : 7 of 7

